

2SC2632

Silicon NPN epitaxial planer type

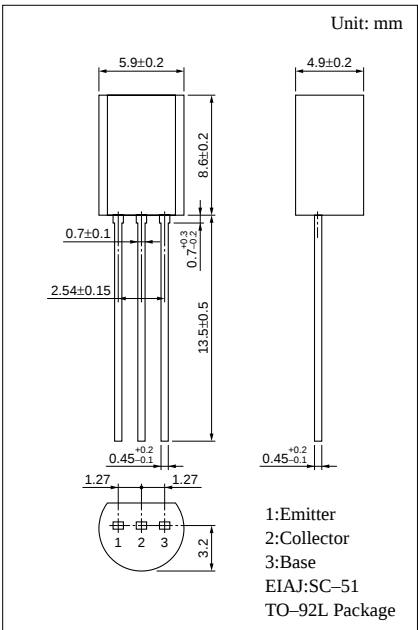
For low-frequency high breakdown voltage amplification
Complementary to 2SA1124

■ Features

- Satisfactory linearity of forward current transfer ratio h_{FE} .
- High collector to emitter voltage V_{CEO} .
- Small collector output capacitance C_{ob} .

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	150	V
Collector to emitter voltage	V_{CEO}	150	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	100	mA
Collector current	I_C	50	mA
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

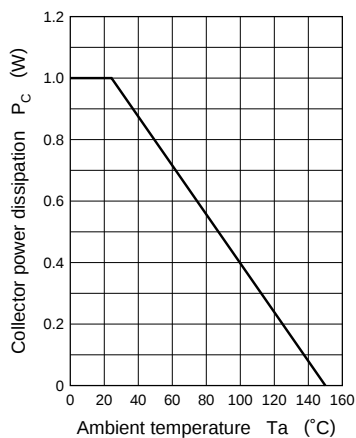
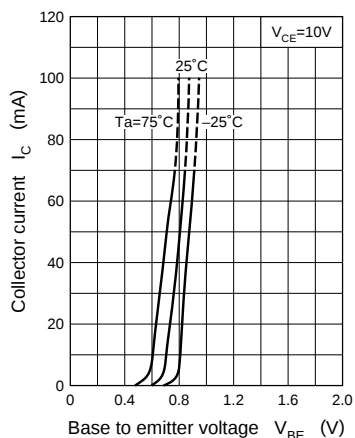
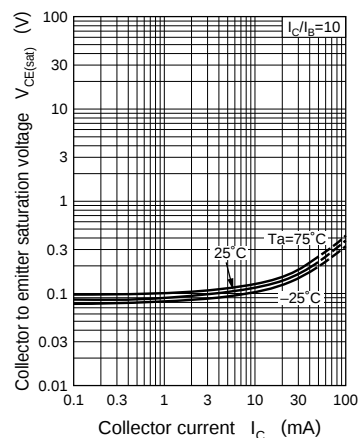
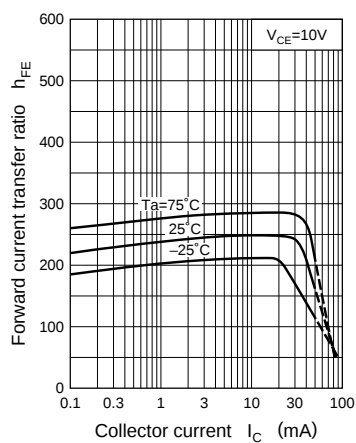
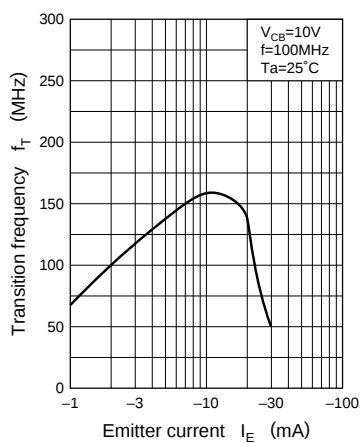


■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 100V, I_E = 0$			1	μA
Collector to emitter voltage	V_{CEO}	$I_C = 0.1mA, I_B = 0$	150			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 5V, I_C = 10mA$	130		330	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30mA, I_B = 3mA$			1	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$		160		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$			3	pF
Noise voltage	NV	$V_{CE} = 10V, I_C = 1mA, G_v = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$		150	300	mV

* h_{FE} Rank classification

Rank	R	S
h_{FE}	130 ~ 220	185 ~ 330

$P_C - T_a$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 